

## Our work

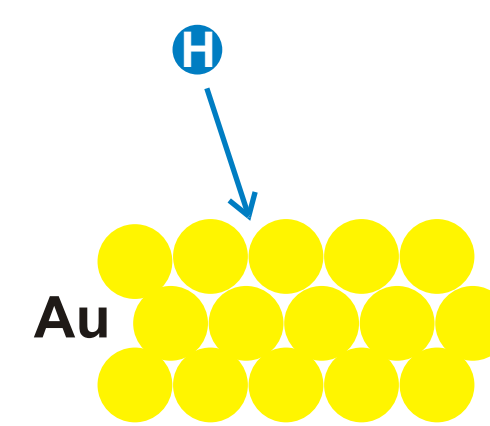
- Studying electronic excitation processes in the course of adsorption, chemisorption and surface reactions
- Understanding the role of single reaction steps in the entire process of chemically induced electronic excitation
- Determination of the excitation energy

## Methods

- Detection of electronic excitation as tunnel current with 0 V tunnel bias in thin metal-insulator-metal junctions
- Characterisation of reaction kinetics by guiding a bunch of atoms or molecules on the surface
- Energy selective detection of the electronic excitation by the application of a bias tunnel voltage
- Comparison of chemically induced excitations with photo excitations

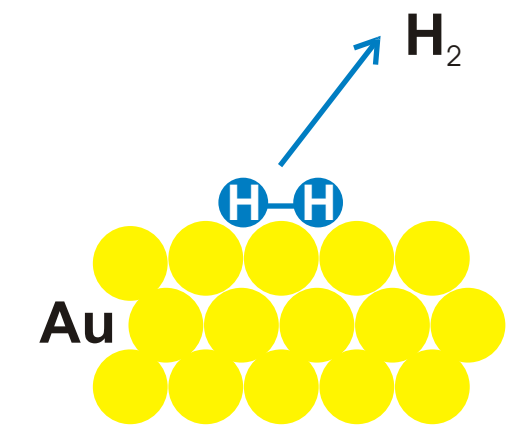
## Some reaction kinetics

### Atomic adsorption



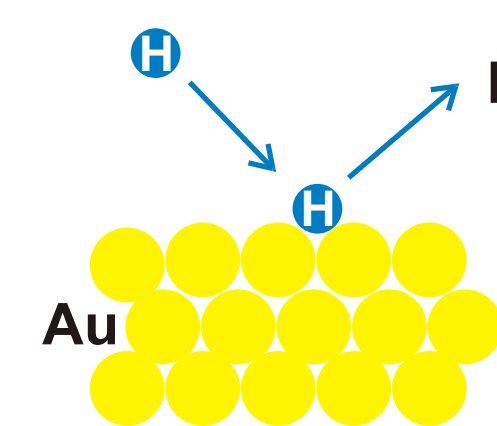
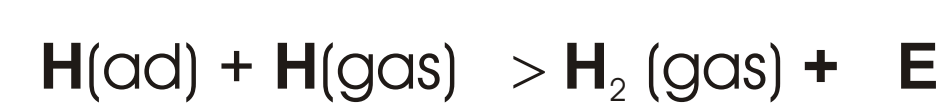
$$\frac{d}{dt} = s j_H \frac{1}{N}$$

### Langmuir-Hinshelwood reaction (LH)



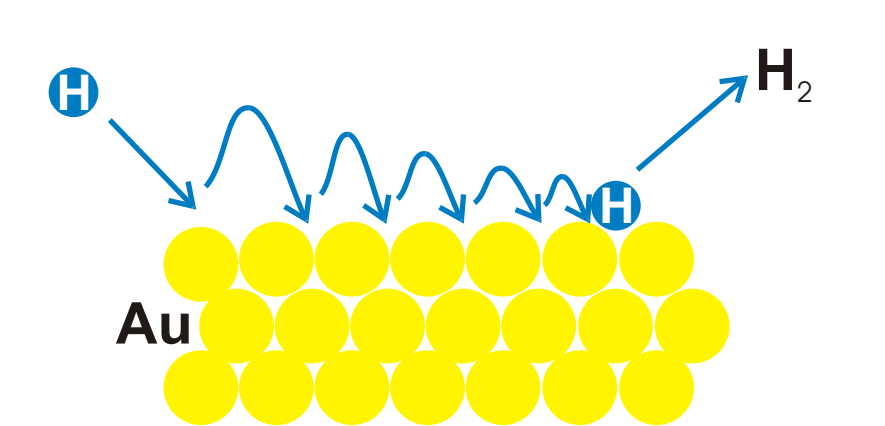
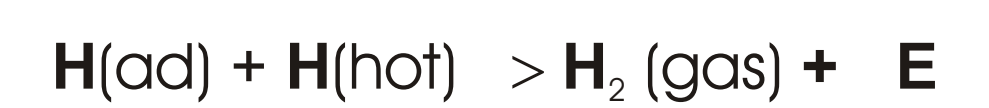
$$\frac{d}{dt} = \frac{1}{N} \cdot \frac{1}{t} \exp\left(-\frac{E_d}{k_B T}\right)$$

### Eley-Rideal reaction (ER)



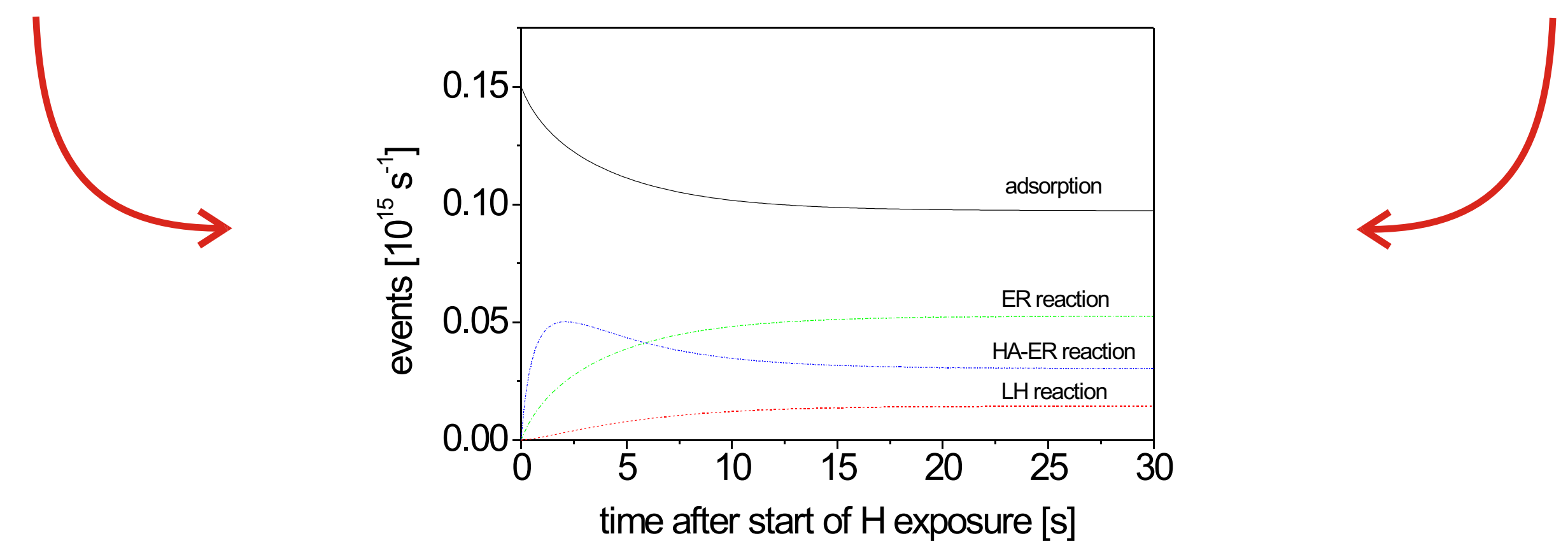
$$\frac{d}{dt} = j_H \frac{1}{N}$$

### Hot atom Eley-Rideal reaction (HA-ER)

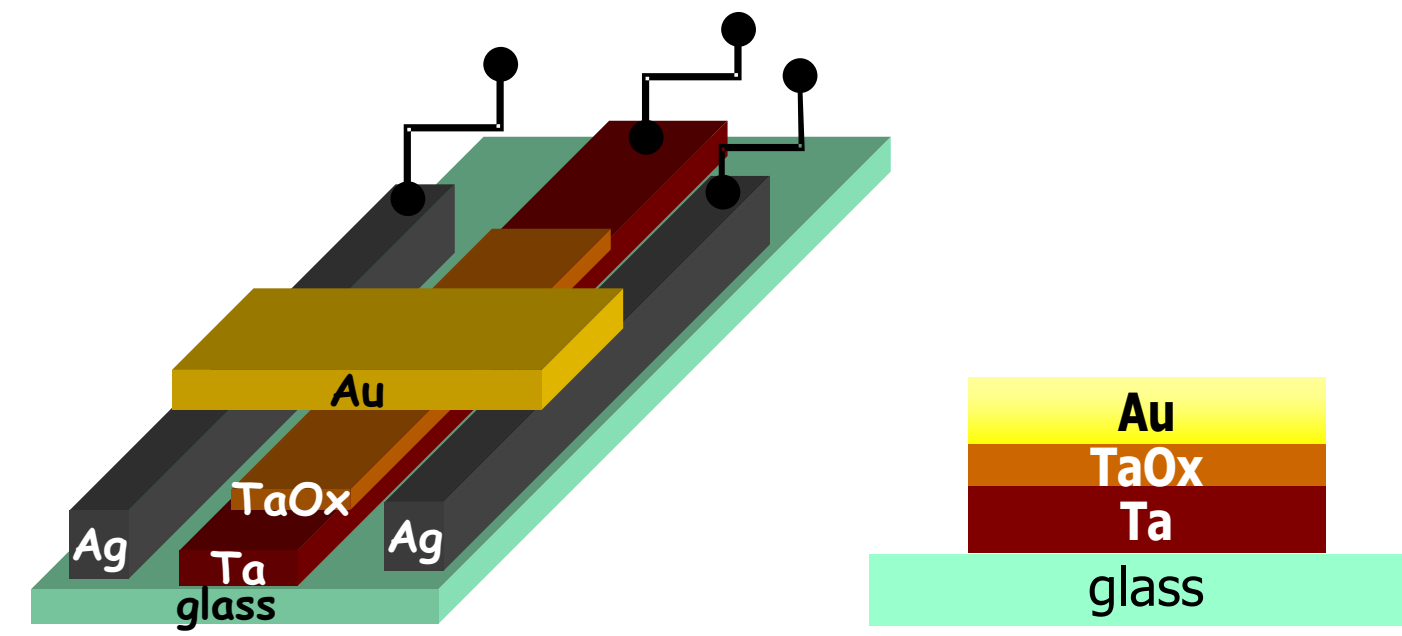
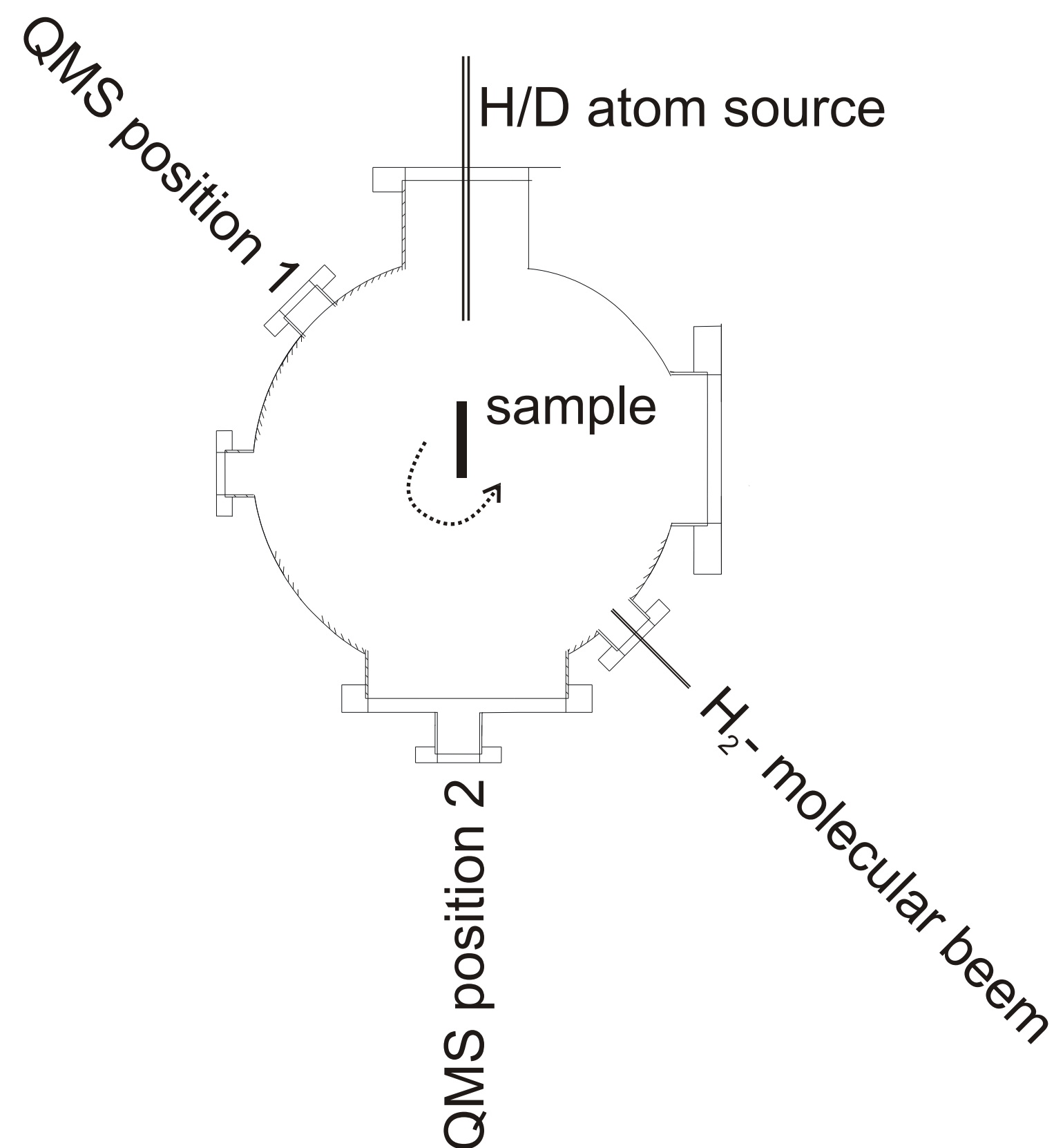


Incident H-atom samples n empty surface sites before reacting with an accommodated H-atom

$$\frac{d\Theta}{dt} = j_H \cdot n \cdot \frac{\Theta}{N} \left(1 - \frac{\Theta}{N}\right)^n$$



## Experimental Setup

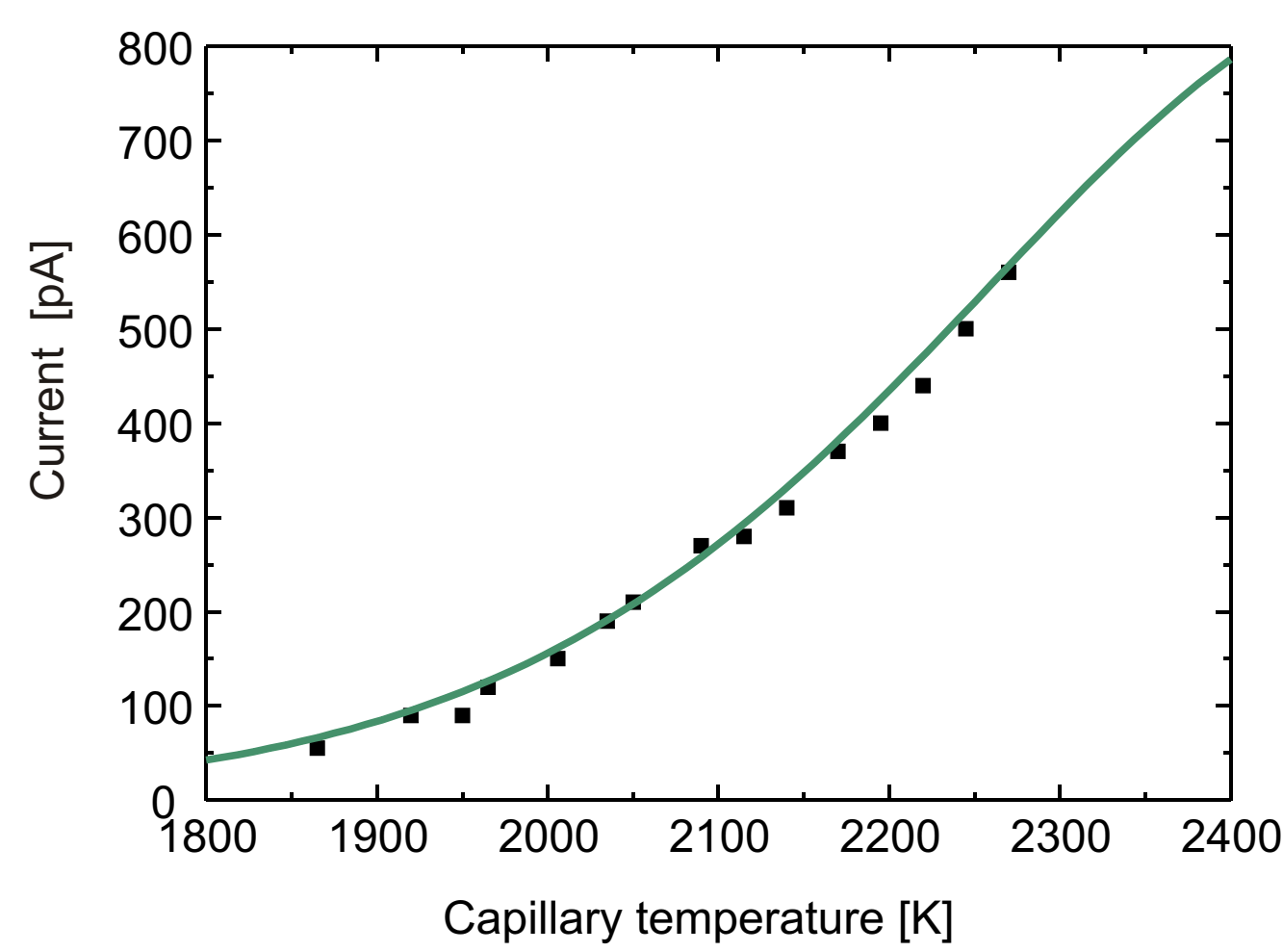
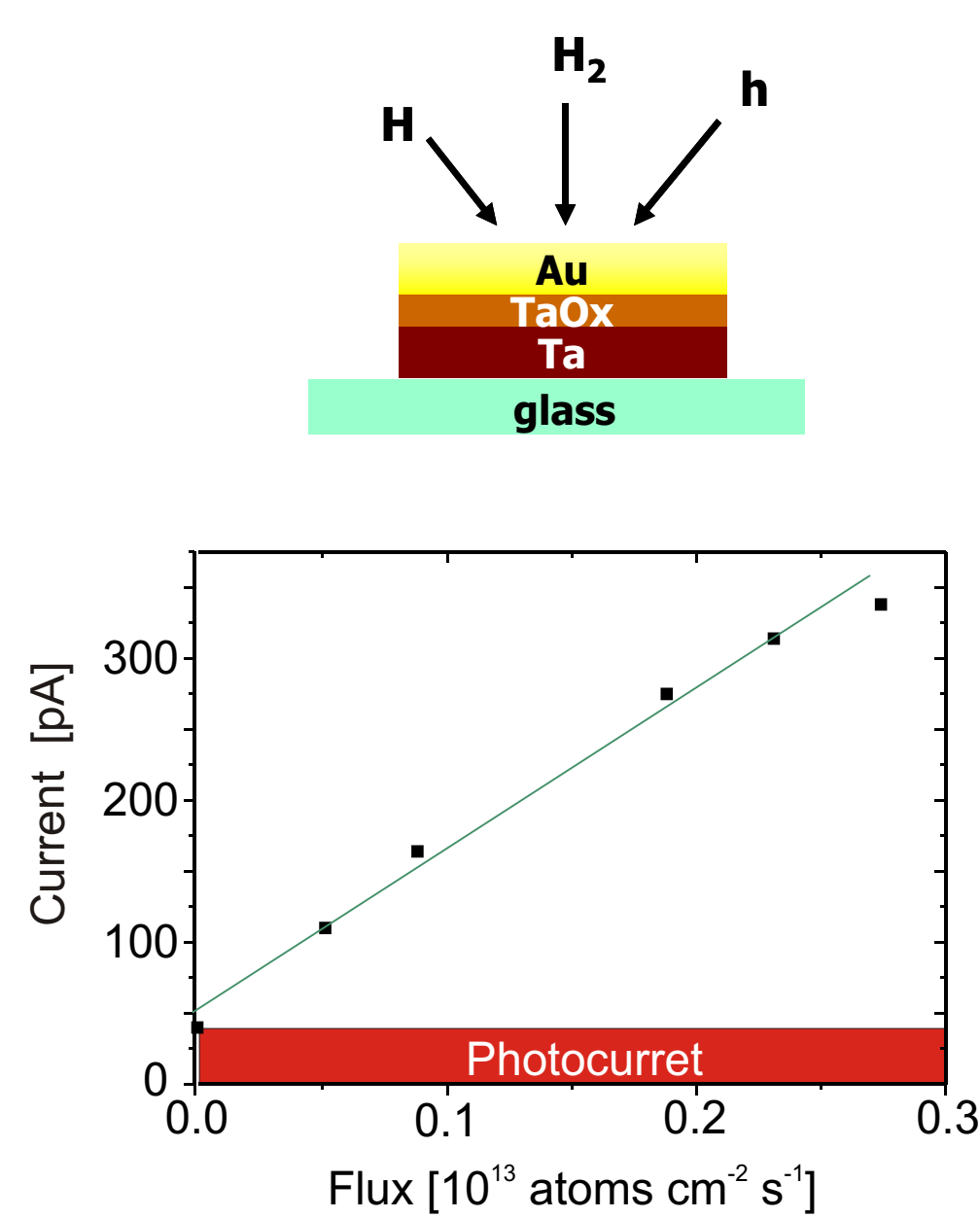


Layer system:

- 30 nm thick tantalum evaporated by e-beam
- 3.4 nm amorphous tantalum oxide produced by local electrochemical oxidation. Thickness adjustable to +/- 0.2
- 15 nm thick gold film in situ prepared in UHV, polycrystalline surface, preferentially 111 oriented

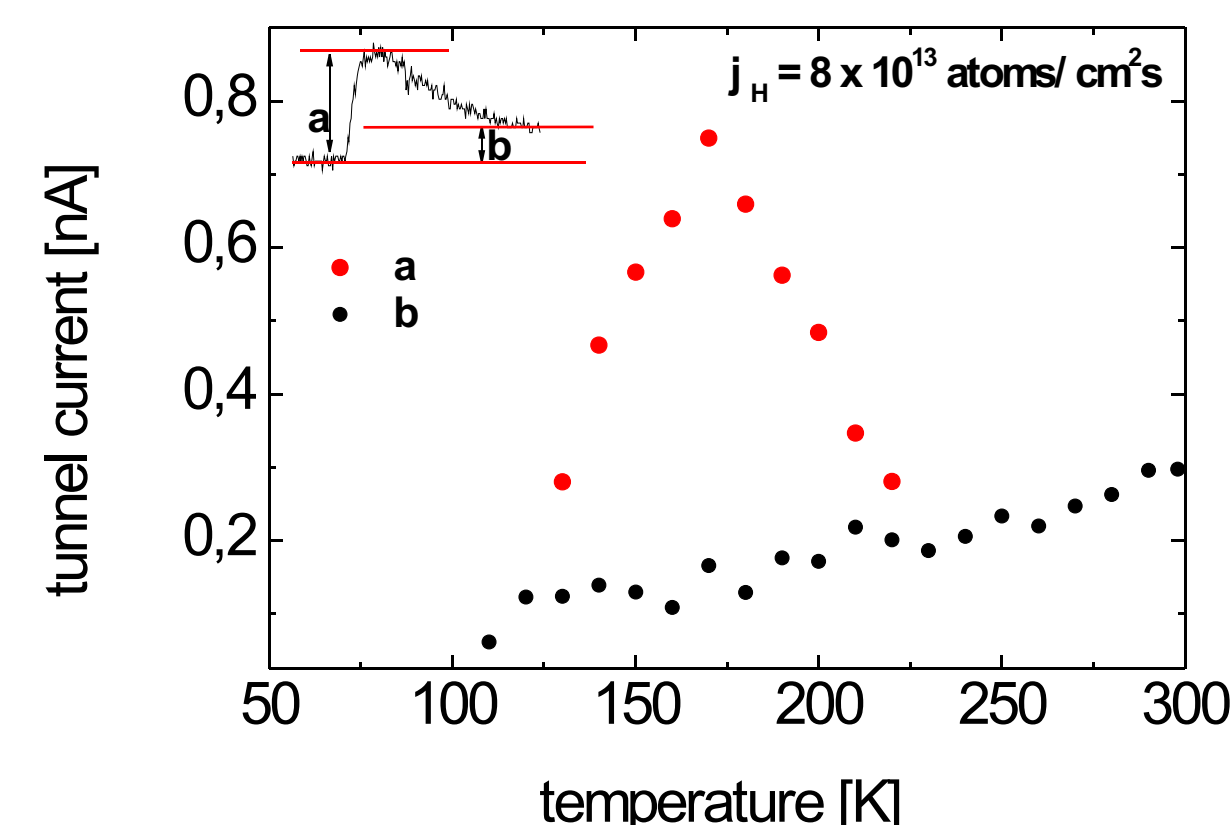
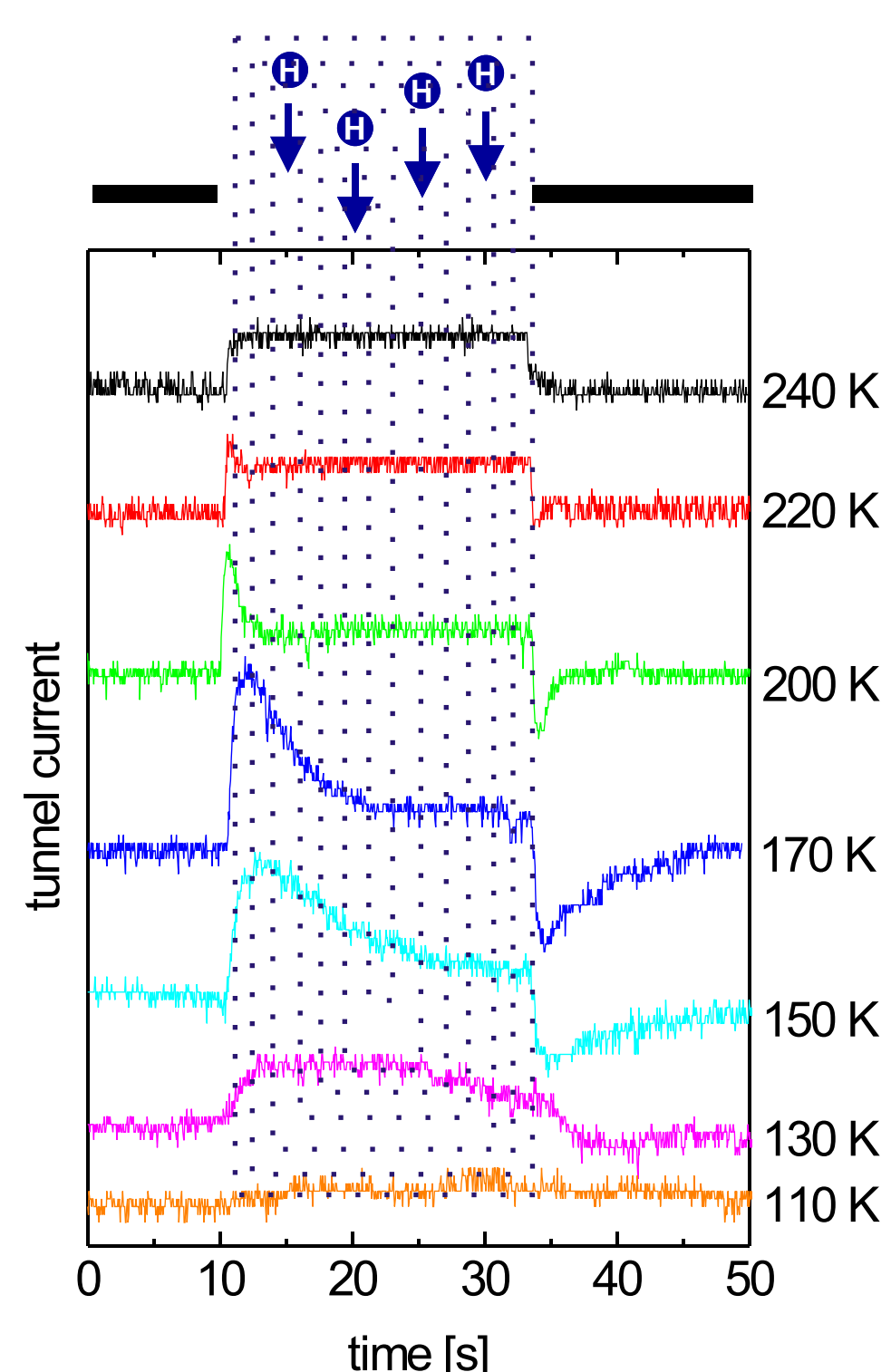
## Experimental results

### Possible sources of the signal



- Capillary induced photocurrent plays minor role
- Tunnel current induced by H atom impact

## Chemically induced tunnel current as a function of sample temperature

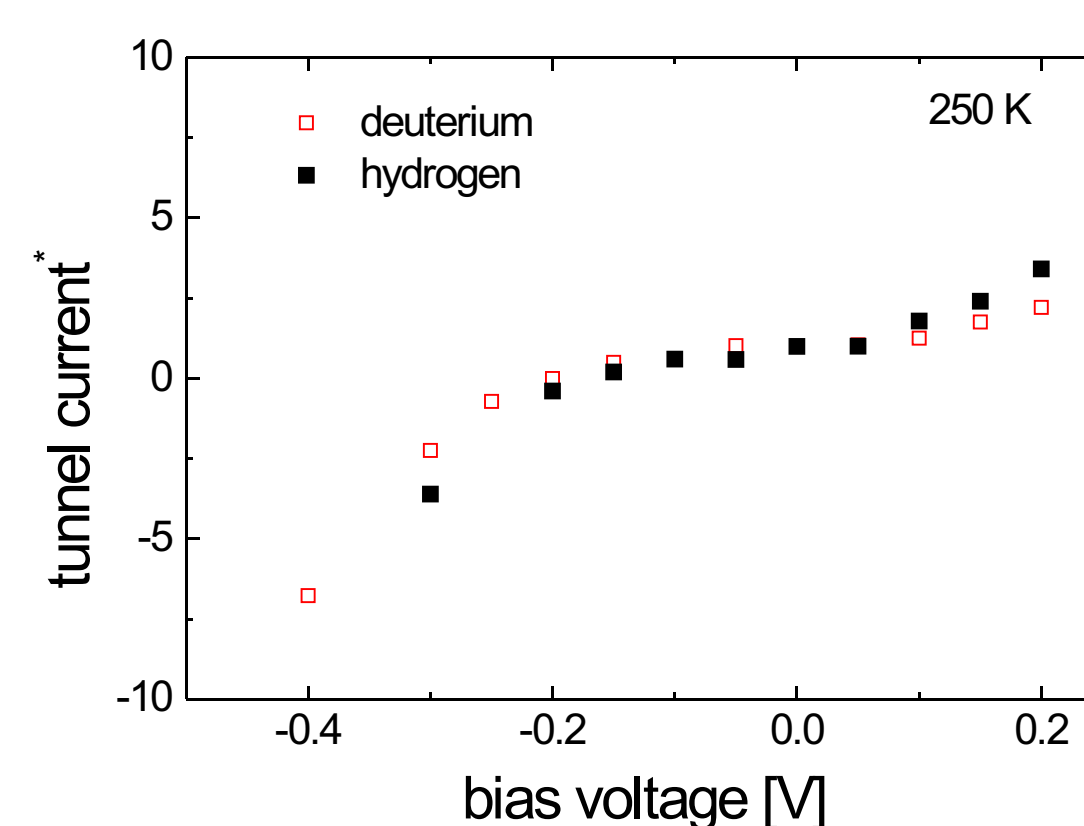


- Prominent overshoot of the tunnel current at the beginning and the end of H exposure in the temperature range 150 - 200 K
- Linear dependence of the steady state signal over the whole temperature range

Simple square form for temperatures  $T > 250$  K

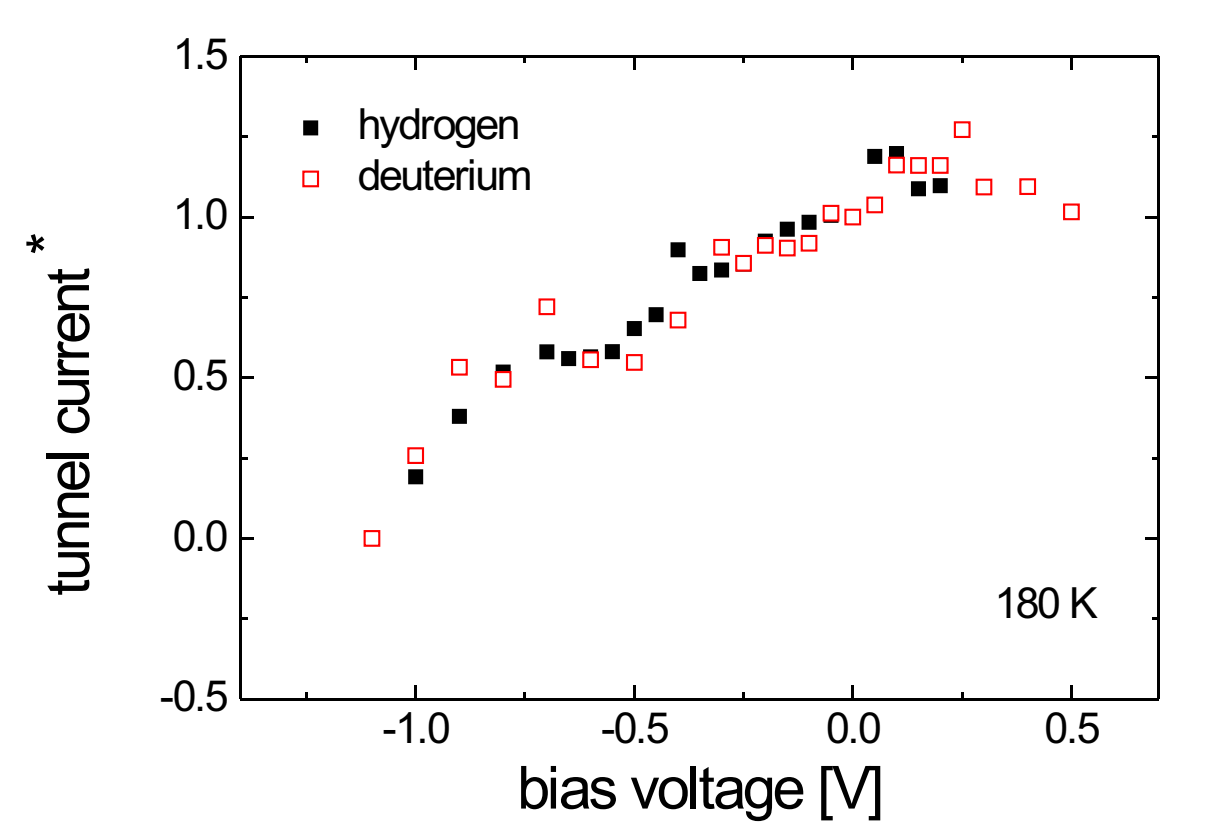
## Energy selective detection of e-h pairs

### In the course of adsorption and LH reactions



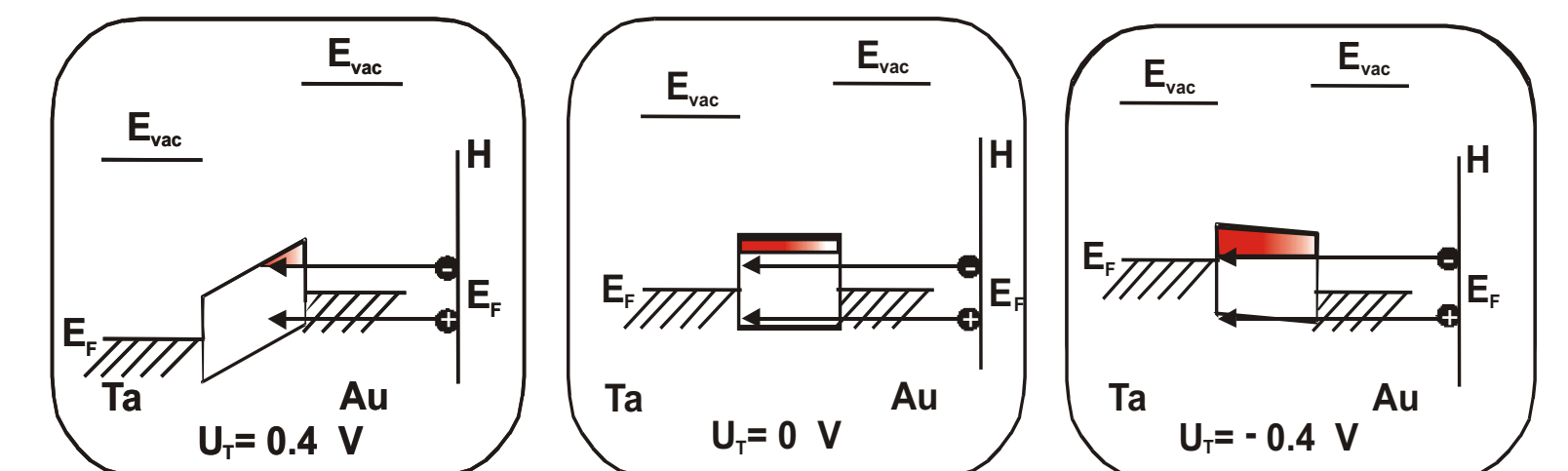
\* normalised at 0 V

### In the course of adsorption and HA-ER reactions



Change of polarity in the H induced tunnel current indicates:

- a simultaneous detection of electrons and holes
- a detection method which acts as a two band tunnel device



## Theoretical consideration

$$f_{\text{excitation}} = A \exp\left(-\frac{(E - E_F)}{k_B T}\right)$$

$f_{\text{excitation}}$  taken to be Maxwell distribution

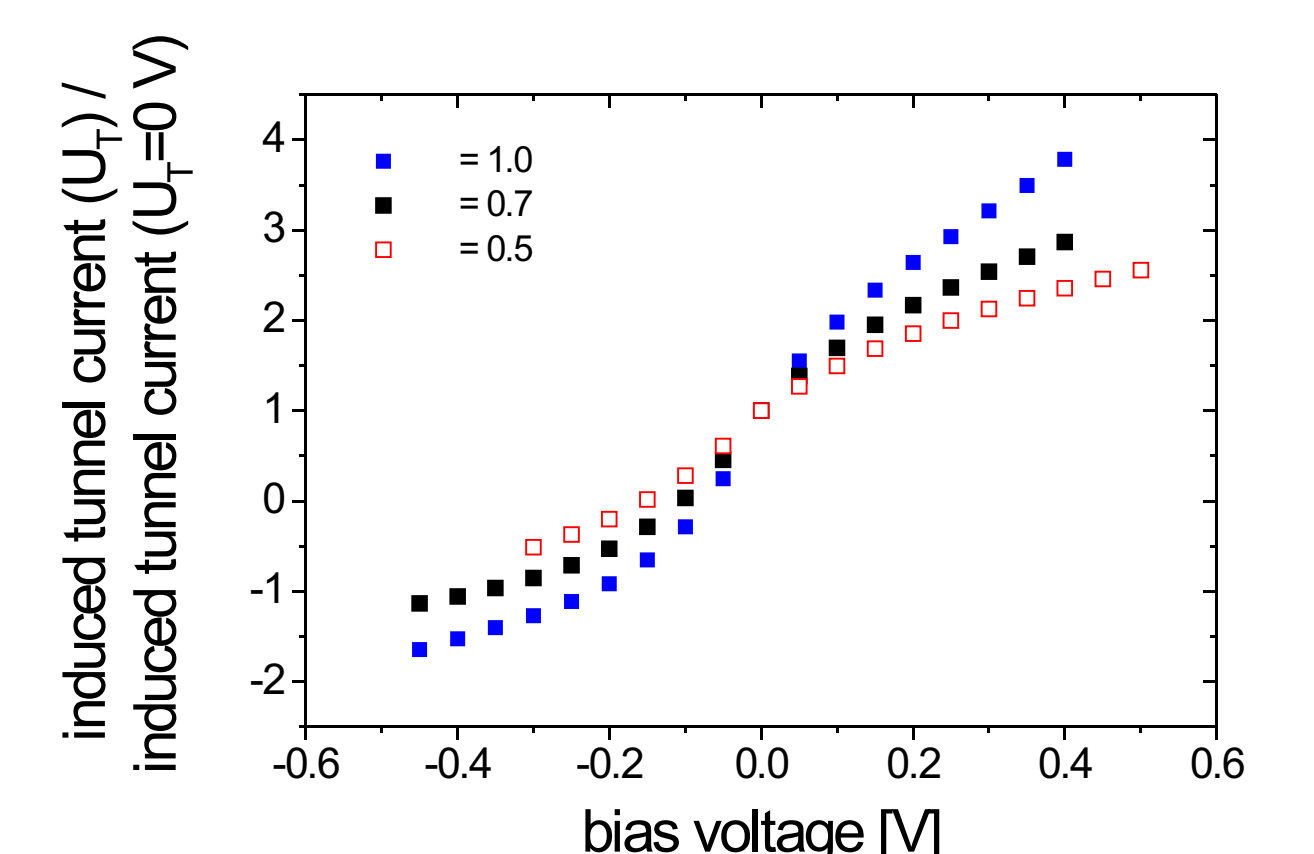
- exactly founded by TDDFT calculations by group E. Pehlke

$$A = 1 \cdot 10^9$$

$$T = 1000 \text{ K}$$

band gap = 4.0 eV

barrier height = 2.0 eV



Small influence of the bias voltage on deuterium induced signal

- wider distribution of excited electrons for D than for H